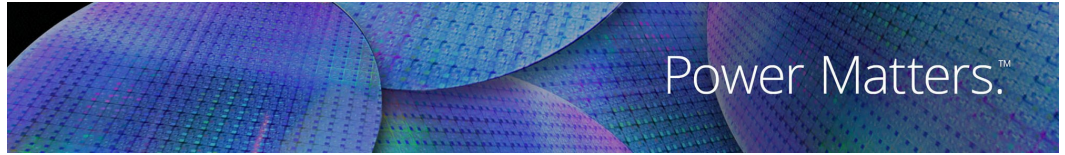


POWER DISCRETES & MODULES

- ▶ Voltage & Current Regulation Diodes
- ▶ Small Signal Diodes and Diode Arrays
- ▶ IGBT
- ▶ Power MOSFET
- ▶ Silicon Carbide (SiC) Semiconductor
- ▶ Power Modules
- ▶ JFET
- ▶ BJT (BiPolar Junction Transistor)
 - BJT Modules (Power Integrated Circuit, PIC)
 - Darlington Transistors
 - Darlington Transistor Array
 - NPN PNP Complimentary Transistor
 - NPN Transistor
 - **PNP Transistor**
- ▶ Legacy Power Discretets & Modules
- ▶ Diode and Rectifier Devices



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JAN2N4957UB (#76659)

Product Status
■ In Production

Overview Resources Ordering Support

The 2N4957UB is a military qualified silicon PNP amplifier transistor designed for VHF-UHF equipment and other high-reliability applications. Common applications include high gain low noise amplifier; oscillator, and mixer applications. It is also available in a low-profile TO-72 leaded package.

Package Waffle Pack
 Carrier:

Electrical Rating	Symbol	Min	Typ	Max	Unit
DC Current Gain	HFE	30		165	

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector Current (dc)	I _C			0.03	A
Collector-Emitter Voltage (Base Open)	V _{CEO}			30	V
Junction Temperature (°C)	T _J			200	°C

Alphanumeric Parameter	Value
Quality Level	JAN

This part can be found in the following product categories:

- Power Discretets & Modules ▶ BJT (BiPolar Junction Transistor) ▶ PNP Transistor
- Power Discretets & Modules ▶ BJT (BiPolar Junction Transistor)